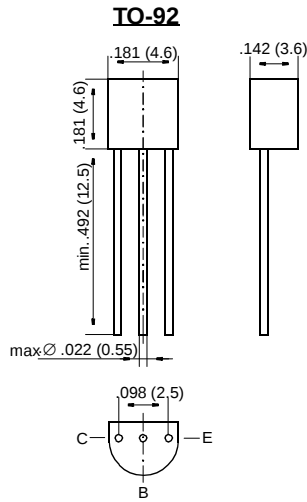


BC546 THRU BC549

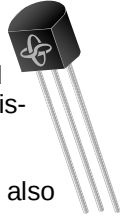
Small Signal Transistors (NPN)



Dimensions in inches and (millimeters)

FEATURES

- ◆ NPN Silicon Epitaxial Planar Transistors
- ◆ These transistors are subdivided into three groups A, B and C according to their current gain. The type BC546 is available in groups A and B, however, the types BC547 and BC548 can be supplied in all three groups. The BC549 is a low-noise type and available in groups B and C. As complementary types, the PNP transistors BC556 ... BC559 are recommended.
- ◆ On special request, these transistors are also manufactured in the pin configuration TO-18.



MECHANICAL DATA

Case: TO-92 Plastic Package

Weight: approx. 0.18 g

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Value	Unit
Collector-Base Voltage	BC546 V_{CBO}	80	V
	BC547 V_{CBO}	50	V
	BC548, BC549 V_{CBO}	30	V
Collector-Emitter Voltage	BC546 V_{CES}	80	V
	BC547 V_{CES}	50	V
	BC548, BC549 V_{CES}	30	V
Collector-Emitter Voltage	BC546 V_{CEO}	65	V
	BC547 V_{CEO}	45	V
	BC548, BC549 V_{CEO}	30	V
Emitter-Base Voltage	BC546, BC547 V_{EBO}	6	V
	BC548, BC549 V_{EBO}	5	V
Collector Current	I_C	100	mA
Peak Collector Current	I_{CM}	200	mA
Peak Base Current	I_{BM}	200	mA
Peak Emitter Current	$-I_{EM}$	200	mA
Power Dissipation at $T_{amb} = 25\text{ °C}$	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_S	-65 to +150	°C

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

BC546 THRU BC549

ELECTRICAL CHARACTERISTICS

	Symbol	Min.	Typ.	Max.	Unit
h-Parameters at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$, $f = 1\text{ kHz}$, Small Signal Current Gain					
Current Gain Group A	h_{fe}	—	220	—	—
B	h_{fe}	—	330	—	—
C	h_{fe}	—	600	—	—
Input Impedance Current Gain Group A	h_{ie}	1.6	2.7	4.5	$k\Omega$
B	h_{ie}	3.2	4.5	8.5	$k\Omega$
C	h_{ie}	6	8.7	15	$k\Omega$
Output Admittance Current Gain Group A	h_{oe}	—	18	30	μS
B	h_{oe}	—	30	60	μS
C	h_{oe}	—	60	110	μS
Reverse Voltage Transfer Ratio					
Current Gain Group A	h_{re}	—	$1.5 \cdot 10^{-4}$	—	—
B	h_{re}	—	$2 \cdot 10^{-4}$	—	—
C	h_{re}	—	$3 \cdot 10^{-4}$	—	—
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 10\mu A$					
Current Gain Group A	h_{FE}	—	90	—	—
B	h_{FE}	—	150	—	—
C	h_{FE}	—	270	—	—
at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$					
Current Gain Group A	h_{FE}	110	180	220	—
B	h_{FE}	200	290	450	—
C	h_{FE}	420	500	800	—
at $V_{CE} = 5\text{ V}$, $I_C = 100\text{ mA}$					
Current Gain Group A	h_{FE}	—	120	—	—
B	h_{FE}	—	200	—	—
C	h_{FE}	—	400	—	—
Thermal Resistance Junction to Ambient Air	R_{thJA}	—	—	250 ¹⁾	K/W
Collector Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ at $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{CEsat} V_{CEsat}	— —	80 200	200 600	mV mV
Base Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$ at $I_C = 100\text{ mA}$, $I_B = 5\text{ mA}$	V_{BEsat} V_{BEsat}	— —	700 900	— —	mV mV
Base-Emitter Voltage at $V_{CE} = 5\text{ V}$, $I_C = 2\text{ mA}$ at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$	V_{BE} V_{BE}	580 —	660 —	700 720	mV mV
Collector-Emitter Cutoff Current at $V_{CE} = 80\text{ V}$ at $V_{CE} = 50\text{ V}$	I_{CES} I_{CES}	— —	0.2 0.2	15 15	nA nA
at $V_{CE} = 30\text{ V}$ BC548, BC549	I_{CES}	—	0.2	15	nA
at $V_{CE} = 80\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$ BC546 at $V_{CE} = 50\text{ V}$, $T_j = 125\text{ }^\circ\text{C}$ BC547	I_{CES} I_{CES}	— —	— —	4 4	μA μA

¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 2 mm from case

BC546 THRU BC549

ELECTRICAL CHARACTERISTICS

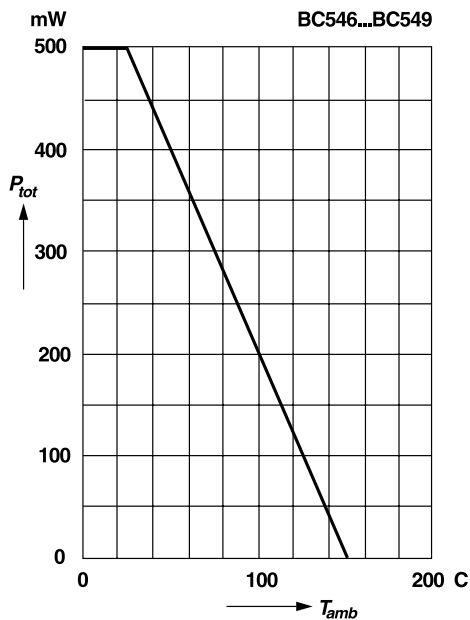
Ratings at 25 °C ambient temperature unless otherwise specified

	Symbol	Min.	Typ.	Max.	Unit
at $V_{CE} = 30 \text{ V}$, $T_j = 125 \text{ °C}$ BC548, BC549	I_{CES}	—	—	4 4	μA μA
Gain-Bandwidth Product at $V_{CE} = 5 \text{ V}$, $I_C = 10 \text{ mA}$, $f = 100 \text{ MHz}$	f_T	—	300	—	MHz
Collector-Base Capacitance at $V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{CBO}	—	3.5	6	pF
Emitter-Base Capacitance at $V_{EB} = 0.5 \text{ V}$, $f = 1 \text{ MHz}$	C_{EBO}	—	9	—	pF
Noise Figure at $V_{CE} = 5 \text{ V}$, $I_C = 200 \mu\text{A}$, $R_G = 2 \text{ k}\Omega$, $f = 1 \text{ kHz}$, $\Delta f = 200 \text{ Hz}$ BC546, BC547	F	—	2	10	dB
BC548	F	—	1.2	4	dB
BC549	F	—	1.4	4	dB

RATINGS AND CHARACTERISTIC CURVES BC546 THRU BC549

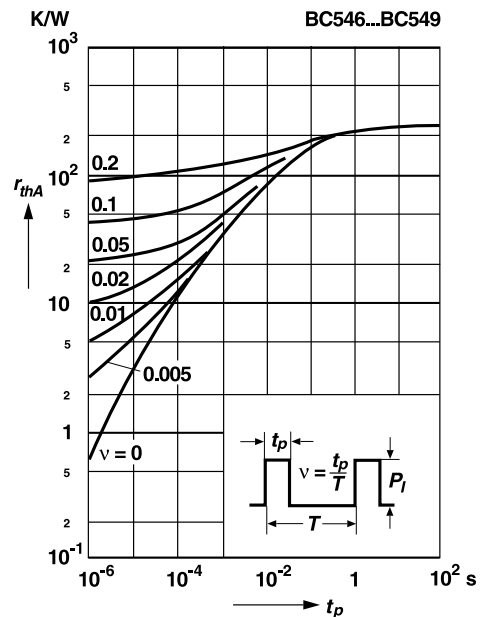
Admissible power dissipation versus temperature

Valid provided that leads are kept at ambient
temperature at a distance of 2 mm from case



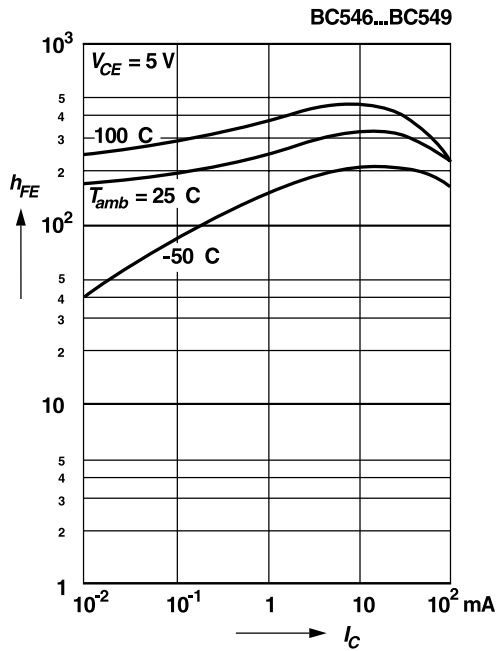
Pulse thermal resistance versus pulse duration

Valid provided that leads are kept at ambient
temperature at a distance of 2 mm from case

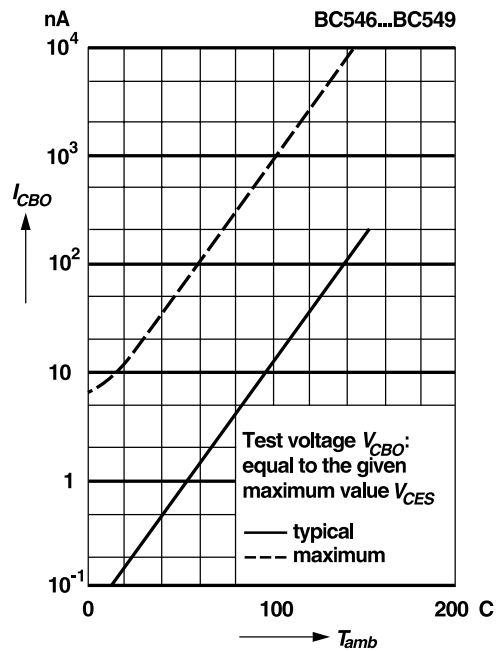


RATINGS AND CHARACTERISTIC CURVES BC546 THRU BC549

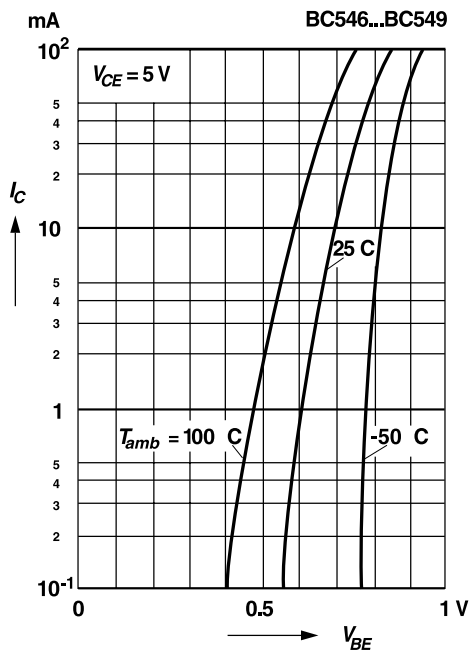
DC current gain
versus collector current



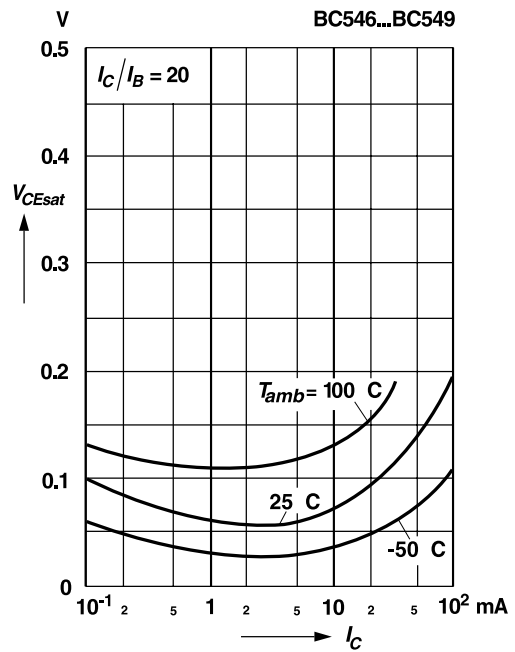
Collector-base cutoff current
versus ambient temperature



Collector current versus
base-emitter voltage

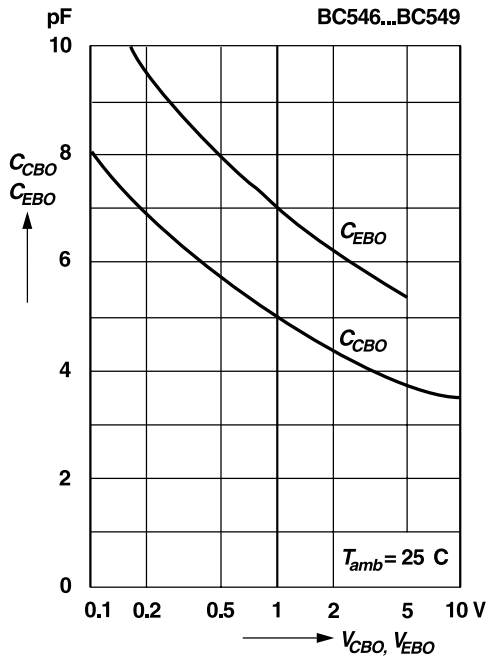


Collector saturation voltage
versus collector current

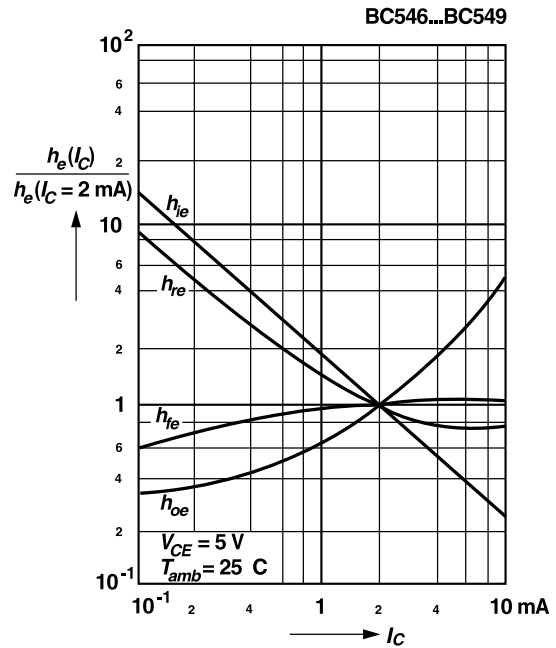


RATINGS AND CHARACTERISTIC CURVES BC546 THRU BC549

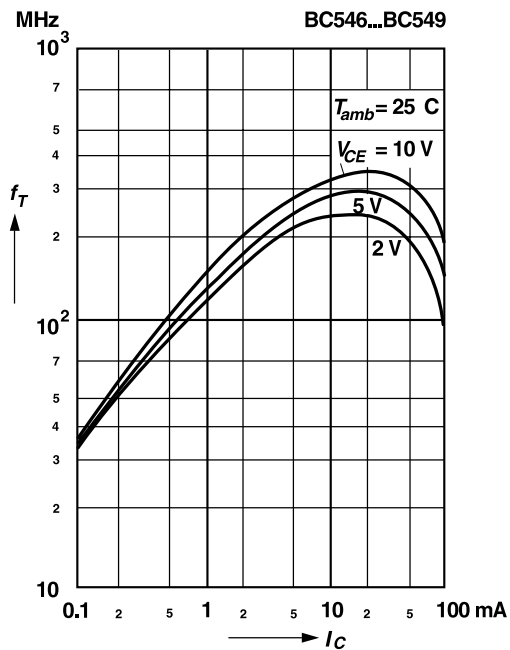
Collector-base capacitance,
Emitter-base capacitance
versus reverse bias voltage



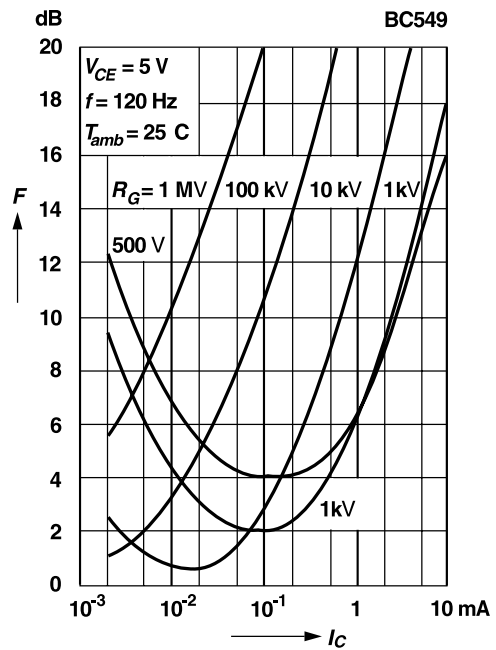
Relative h-parameters
versus collector current



Gain-bandwidth product
versus collector current

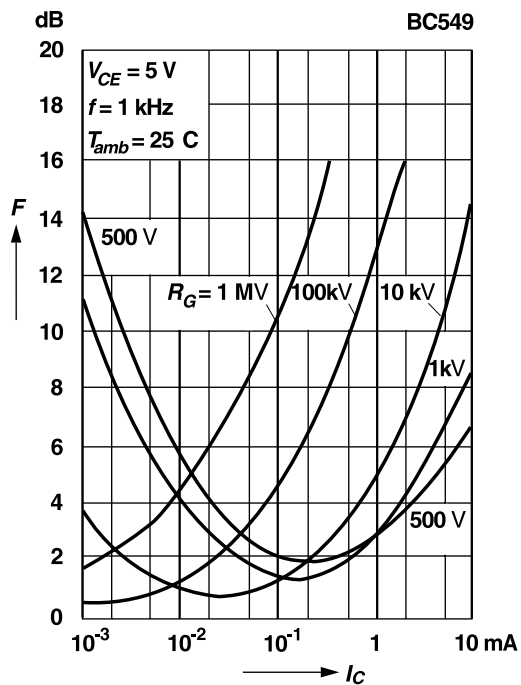


Noise figure
versus collector current



RATINGS AND CHARACTERISTIC CURVES BC546 THRU BC549

Noise figure
versus collector current



Noise figure
versus collector emitter voltage

